Sheet 1 of 1. FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE ATTY. DOCKET NO. APPLICATION NO. PATENT AND TRADEMARK OFFICE 26860/33:43D 08/959,140 NFORMATION DISCLOSURE CITATION APPLICANT Yunlong Sun and Edward J. Swenson (Use several sheets if necessary) JAN - 5 1998 FILING DATE **GROUP** October 28, 1997 **U.S. PATENT DOCUMENTS EXAMINER** DOCUMENT FILING DATE INITIAL NUMBER DATE **NAME CLASS SUBCLASS** IF APPROPRIATE AA 04/22/97 Fischer et al. 315 200 08/11/95 02/09/93 AB 8 Fischer et al. 437 173 09/06/91 GÉ 0 AC 6 11/19/91 Fischer et al. 357 51 8 4 5 3 AD 08/01/91 Fischer 357 51 8 ΑE 1 0 0 4 9 03/07/89 Fischer et al. 350 96.12 AF 9 8 0 3 5 07/01/86 Fischer et al. 430 323 2 AG 4 2 8 5 2 8 10/14/80 Cenker et al. 365 200 AH FOREIGN PATENT DOCUMENTS TRANSLATION **DOCUMENT NUMBER** DATE **COUNTRY CLASS SUBCLASS** YES NO ΑI AJ OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) 1988 "Laser Programming of Gallium Arsenide HFET Digital Integrated Circuits," Fischer ΑK 1981 "Laser Programmable Redundancy and Yield Improvement in a 64K DRAM," Smith et al AL 1980 "Trimming Behavior and Post-Trim Characteristics of Ta2N resistors on Silicon," Kestenbaum and Baer AM 1979 "Interference Effects in Laser Micromachining of Thin Films on Silicon," Kestenbaum AN 1979 "A Fault-Tolerant 64K Dynamic Random-Access Memory," Cenker et al. AO 1976 "Laser Coding of Bipolar Read-Only Memories," North and Weick £56 AP

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Yunlong Sun and Edward J. Swenson

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